IN THE SPECIFICATION

Please amend the specification as follows:

Page 7, the paragraph beginning at line 16:

In other aspect, the invention provides a method of fabricating an electroluminescent device including the steps of:

(i) implanting a surface region of a silicon wafer, doped with a donor impurity to render the wafer n-type, with an acceptor impurity such that the surface region has a volume concentration of the acceptor impurity which is greater than a volume concentration of the donor impurity;

(ii) anodizing the wafer under illumination to provide a luminescent porous silicon region extending through the surface region; and

(iii) depositing an electrode on the porous silicon region;

characterized in that the surface region has a sheet resistivity greater than ~~100 Ω~~$^{+}$ 100 Ω per square immediately prior to the anodizing step.

Page 13, the paragraph beginning at line 12:

Measurements of the sheet resistivities of the heavily doped region 28 after annealing and of the front face after ion implantation have been made. The region 28 had a sheet resistivity of 16 ~~Ω...~~$^{+}$ Ω per square, which compares with an estimated value for a fully activated dopant implant of 10 ~~Ω~~$^{+}$ Ω per square. Therefore, within experimental error, the dopant in the heavily doped region 28 is fully activated. After ion implantation,

the front face had a sheet resistivity of 1800 ~~Ω~~ + Ω per square, compared with an estimated value of 10 ~~Ω~~ + Ω per square if the dopant had been fully activated. The conductivity of the unannealed implanted boron layer is less than 1% the expected conductivity if the dopant had been fully electrically activated. Transmission electron microscopy has indicated that the crystalline structure of the implanted silicon is heavily damaged by the boron ion implantation.

B2 comp.

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